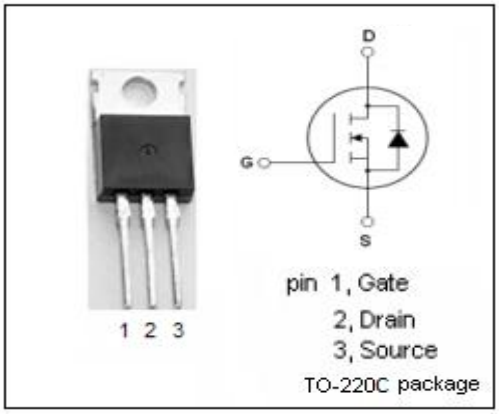
isc N-Channel MOSFET Transistor SPP12N50C3，ISPP12N50C3



• FEATURES

- Static drain-source on-resistance:
  R_{DS}(on) ≤0.38Ω
- Enhancement mode
- Fast Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• DESCRITION

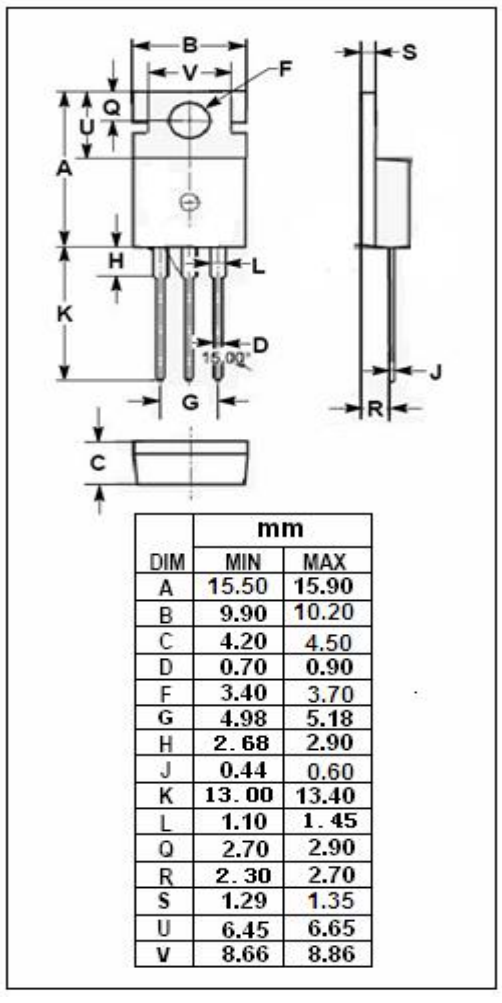
- New revolutionary high voltage technology
- Ultra low effective capacitance

• ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	500	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current-Continuous	11.6	A
I_{DM}	Drain Current-Single Pulsed	34.8	A
P_D	Total Dissipation @T_C=25℃	125	W
T_j	Max. Operating Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	1	℃/W
Rth(ch-a)	Channel-to-ambient thermal resistance	62	℃/W



DIM	mm MIN	MAX
A	15.50	15.90
B	9.90	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	13.00	13.40
L	1.10	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V; I_D =250 μ A	500			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}; I_D =500 μ A	2.1		3.9	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}=10V; I_D=7A			0.38	Ω
I_{GSS}	Gate-Source Leakage Current	V_{GS}=20V; V_{DS}=0V			0.1	μ A
I_{DSS}	Drain-Source Leakage Current	V_{DS}=500V; V_{GS}= 0V			1	μ A
V_{SD}	Diode forward voltage	I_F=I_S; V_{GS} = 0V			1.2	V